30 SEP 2003

162162

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
14 February 2002 (14.02.2002)

PCT

(10) International Publication Number
WO 02/13258 A2

(51) International Patent Classification[7]: H01L 21/768

(21) International Application Number: PCT/US01/23571

(22) International Filing Date: 26 July 2001 (26.07.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/633,931 8 August 2000 (08.08.2000) US

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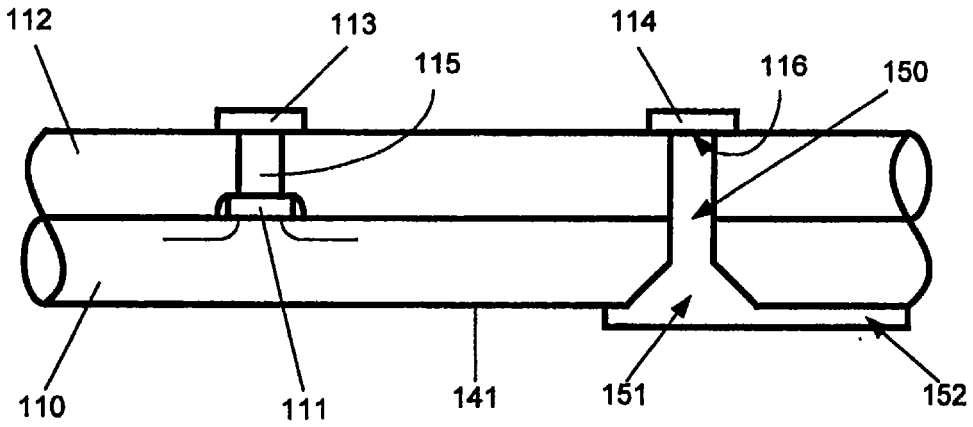
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *without international search report and to be republished upon receipt of that report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: BACKSIDE CONTACT FOR INTEGRATED CIRCUIT AND METHOD OF FORMING SAME



(57) Abstract: A contact (146) formed from the backside of an integrated circuit device includes a first conductive layer (114) on a first surface of the integrated circuit device and a second conductive layer on a second surface (141) of the device. The two conductive layers are coupled by way of an opening (144) through the semiconductor substrate (110) separating the two conductive layers. A method for making the backside contact (146) comprises forming the first conductive layer (114), forming an opening (144) through the semiconductor substrate (110) to expose at least a portion of the underside (116) of the first conductive layer (114), then filling the opening (144) with a conductive material (150) to provide an electrical contact to the first conductive layer (114) from the backside of the integrated circuit device.

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